XP131A1330SR

ETR1103_001

Power MOSFET

■GENERAL DESCRIPTION

The XP131A1330SR is an N-channel Power MOSFET with low on-state resistance and ultra high-speed switching characteristics

Because high-speed switching is possible, the IC can be efficiently set thereby saving energy.

The small SOP-8 package makes high density mounting possible.

■APPLICATIONS

- ●Notebook PCs
- ●Cellular and portable phones
- ●On-board power supplies
- ●Li-ion battery systems

■FEATURES

Low On-State Resistance: Rds(on)=0.03Ω(Vgs=4.5V)
: Rds(on)=0.04Ω(Vgs=2.5V)
: Rds(on)=0.07Ω(Vgs=1.5V)

Ultra High-Speed Switching

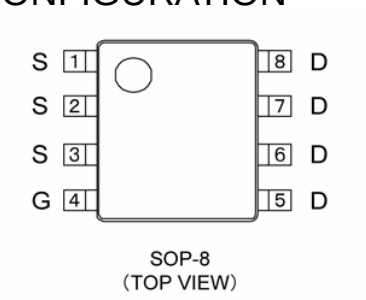
Driving Voltage : 1.5V

N-Channel Power MOSFET

DMOS Structure

Package : SOP-8

■PIN CONFIGURATION

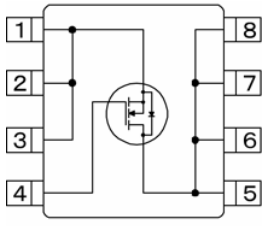


SOP-8
(TOP VIEW)

■PIN ASSIGNMENT

PIN NUMBER	PIN NAME	FUNCTION
1~3	S	Source
4	G	Gate
5~8	D	Drain

■EQUIVALENT CIRCUIT



N-channel MOSFET
(1 device built-in)

■ABSOLUTE MAXIMUM RATINGS

Ta = 25℃

PARAMETER	SYMBOL	RATINGS	UNITS
Drain-Source Voltage	Vdss	20	V
Gate-Source Voltage	Vgss	±8	V
Drain Current (DC)	Id	8	A
Drain Current (Pulse)	Idp	30	A
Reverse Drain Current	Idr	8	A
Channel Power Dissipation *	Pd	2.5	W
Channel Temperature	Tch	150	℃
Storage Temperature Range	Tstg	-55~150	℃

* When implemented on a glass epoxy PCB

■ELECTRICAL CHARACTERISTICS

DC Characteristics

Ta = 25℃

PARAMETER	SYMBOL	CONDITIONS	MIN.	TYP.	MAX.	UNITS
Drain Cut-Off Current	Idss	Vds=20V, Vgs=0V	-	-	10	μA
Gate-Source Leak Current	Igss	Vgs=±8V, Vds=0V	-	-	±1	μA
Gate-Source Cut-Off Voltage	Vgs(off)	Id=1mA, Vds=10V	0.5	-	1.2	V
Drain-Source On-State Resistance *	Rds(on)	Id=4A, Vgs=4.5V	-	0.025	0.03	Ω
		Id=4A, Vgs=2.5V	-	0.030	0.040	Ω
		Id=1A, Vgs=1.5V	-	0.045	0.07	Ω
Forward Transfer Admittance *	| Yfs |	Id=4A, Vds=10V	-	22	-	S
Body Drain Diode Forward Voltage	Vf	If=8A, Vgs=0V	-	0.85	1.1	V

* Effective during pulse test.

Dynamic Characteristics

Ta = 25℃

PARAMETER	SYMBOL	CONDITIONS	MIN.	TYP.	MAX.	UNITS
Input Capacitance	Ciss	Vds=10V, Vgs=0V f=1MHz	-	950	-	pF
Output Capacitance	Coss		-	430	-	pF
Feedback Capacitance	Crss		-	180	-	pF

Switching Characteristics

Ta = 25℃

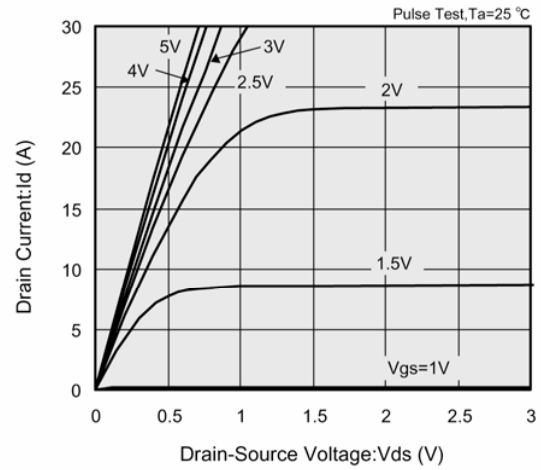
PARAMETER	SYMBOL	CONDITIONS	MIN.	TYP.	MAX.	UNITS
Turn-On Delay Time	td (on)	Vgs=5V, Id=4A Vdd=10V	-	15	-	ns
Rise Time	tr		-	20	-	ns
Turn-Off Delay Time	td (off)		-	80	-	ns
Fall Time	tf		-	15	-	ns

Thermal Characteristics

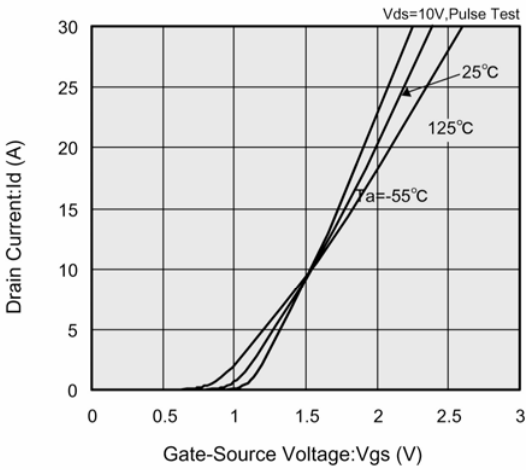
PARAMETER	SYMBOL	CONDITIONS	MIN.	TYP.	MAX.	UNITS
Thermal Resistance (Channel-Ambience)	Rth (ch-a)	Implement on a glass epoxy resin PCB	-	50	-	℃/W

■TYPICAL PERFORMANCE CHARACTERISTICS

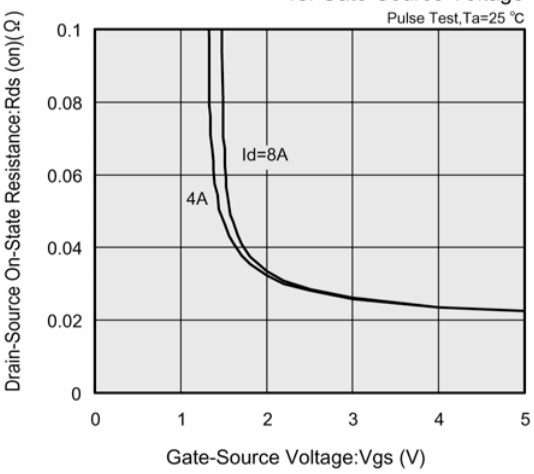
(1) Drain Current vs. Drain-Source Voltage



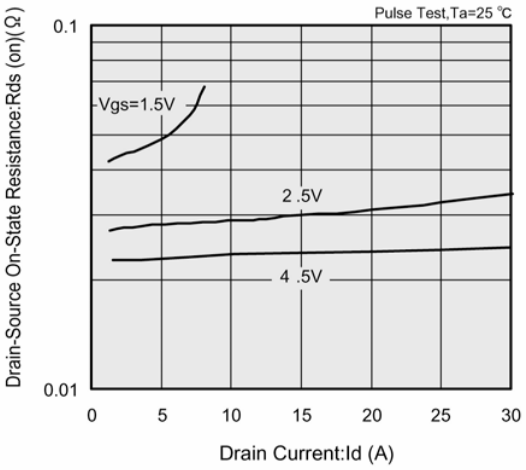
(2) Drain Current vs. Gate-Source Voltage



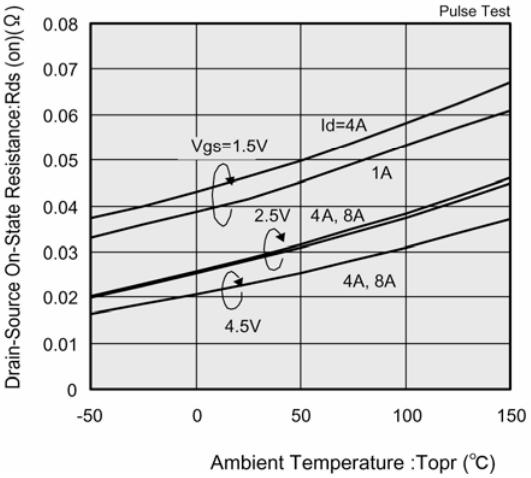
(3) Drain-Source On-State Resistance vs. Gate-Source Voltage



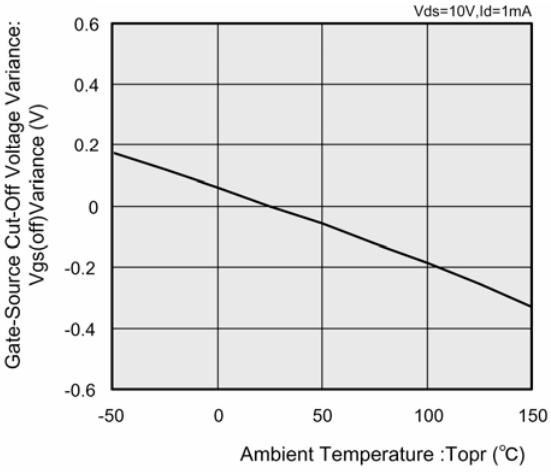
(4) Drain-Source On-State Resistance vs. Drain Current



(5) Drain-Source On-State Resistance vs. Ambient Temperature

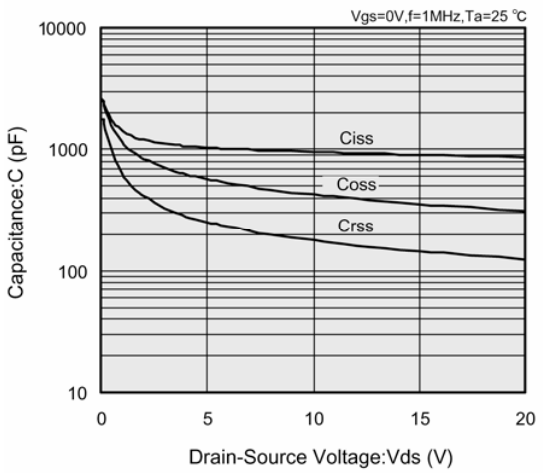


(6) Gate-Source Cut-Off Voltage Variance vs. Ambient Temperature

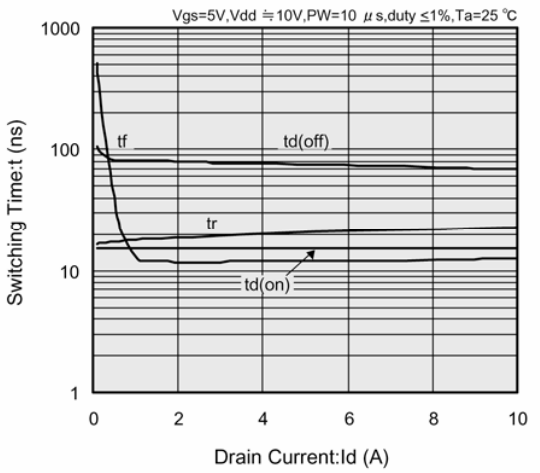


■TYPICAL PERFORMANCE CHARACTERISTICS (Continued)

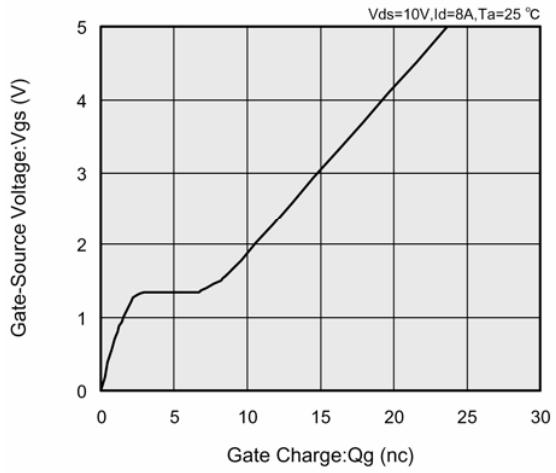
(7) Capacitance vs. Drain-Source Voltage



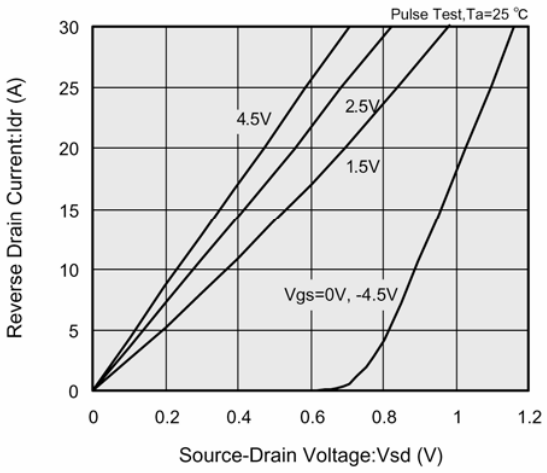
(8) Swiching Time vs. Drain Current



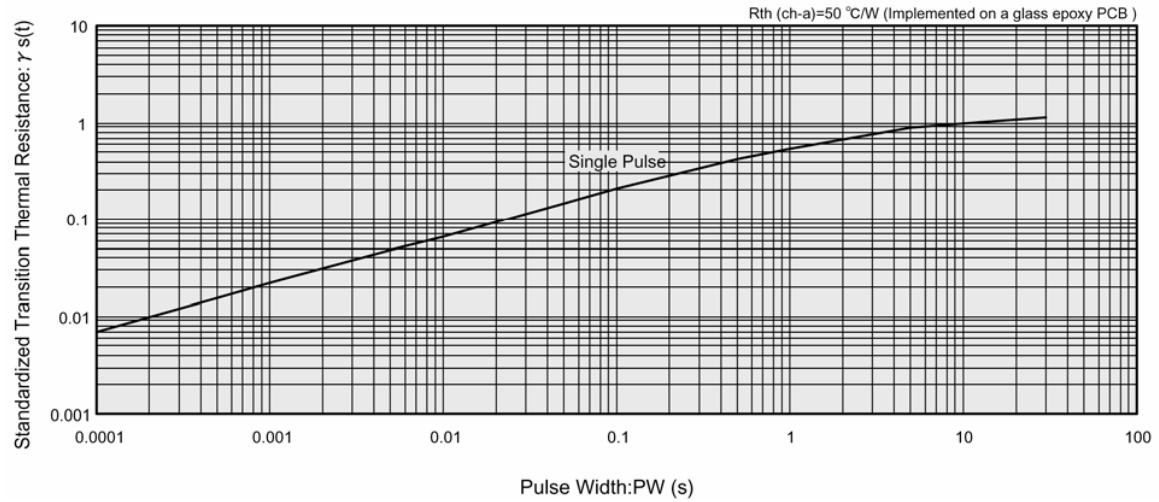
(9) Gate-Source Voltage vs. Gate Charge



(10) Reverse Drain Current vs. Source-Drain Voltage



(11) Standardized transition Thermal Resistance vs. Pulse Width



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